



ALPHA & OMEGA
SEMICONDUCTOR

AOS Semiconductor Product Reliability Report

AO4494/AO4494L, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

**495 Mercury Drive
Sunnyvale, CA 94085
U.S.**

Tel: (408) 830-9742

www.aosmd.com

This AOS product reliability report summarizes the qualification result for AO4494. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4494 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation
- V. Quality Assurance Information

I. Product Description:

The AO4494/L combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON). This device is for PWM applications.

AO4494 and AO4494L are electrically identical.

-RoHS Compliant

-AO4494L is Halogen Free

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter		Symbol	Max.	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	18	A
	$T_A=70^\circ\text{C}$		14	
Pulsed Drain Current		I_{DM}	130	
Avalanche Current		I_{AR}	32	
Repetitive avalanche energy L=0.1mH		E_{AR}	51	mJ
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	3.1	W
	$T_A=70^\circ\text{C}$		2.0	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient	$T \leq 10\text{s}$	$R_{\theta JA}$	28	40	$^\circ\text{C/W}$
	Steady-State		59	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

II. Die / Package Information:

	AO4494	AO4494L (Green Compound)
Process	Standard sub-micron Low voltage N channel process	Standard sub-micron Low voltage N channel process
Package Type	8 leads SOIC	8 leads SOIC
Lead Frame	Cu, S/pad Ag spot	Cu, S/pad Ag spot
Die Attach	Ag epoxy	Ag epoxy
Bond wire	S: Cu 2mils; G: Au 1.3mils	S: Cu 2mils; G: Au 1.3mils
Mold Material	Epoxy resin with silica filler	Epoxy resin with silica filler
Filler % (Spherical/Flake)	90/10	100/0
Flammability Rating	UL-94 V-0	UL-94 V-0
Backside Metallization	Ti / Ni / Ag	Ti / Ni / Ag
Moisture Level	Up to Level 1 *	Up to Level 1 *

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4494 (Standard) & AO4494L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°C Green: 168hr 85°C /85%RH +3 cycle reflow@260°C	0hr	Standard: 83 lots Green: 29 lots	17380 pcs	0
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	2 lots (Note A*)	164 pcs 77+5 pcs / lot	0
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	2 lots (Note A*)	164 pcs 77+5 pcs / lot	0
HAST	130 +/- 2°C , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 81 lots Green: 16 lots (Note B**)	5335 pcs 50+5 pcs / lot	0
Pressure Pot	121°C , 29.7psi, RH=100%	96 hrs	Standard: 83 lots Green: 20 lots (Note B**)	5665 pcs 50+5 pcs / lot	0
Temperature Cycle	-65°C to 150°C , air to air	250 / 500 cycles	Standard: 87 lots Green: 29 lots (Note B**)	6380 pcs 50+5 pcs / lot	0

III. Result of Reliability Stress for AO4494 (Standard) & AO4494L (Green) Continues

DPA	Internal Vision Cross-section X-ray	NA	5	5	0
			5	5	
			5	5	
CSAM		NA	5	5	0
Bond Integrity	Room Temp 150°C bake 150°C bake	0hr 250hr 500hr	40	40 wires	0
			40	40 wires	
			40	40 wires	
Solderability	245°C	5 sec	15	15 leads	0

Note A: The HTGB and HTRB reliability data presents total of available AO4494 and AO4494L burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO4494 and AO4494L comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 64

MTTF = 1774 years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4494). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)]$$

$$= 1.83 \times 10^9 / [2 (2X164) (168) (258)] = 64$$

$$\text{MTTF} = 10^9 / \text{FIT} = 1.55 \times 10^7 \text{hrs} = 1774 \text{ years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [**Af**] = $\text{Exp} [E_a / k (1/T_j u - 1/T_j s)]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, $8.617164 \times 10^{-5} \text{eV} / \text{K}$

V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.

Guaranteed Outgoing Defect Rate: **< 25 ppm**

Quality Sample Plan: conform to **Mil-Std-105D**